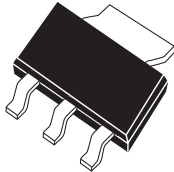


**CBCP68 NPN
CBCP69 PNP**

**SILICON COMPLEMENTARY
SMALL SIGNAL TRANSISTORS**



SOT-223 CASE

CentralTM Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBCP68, CBCP69 types are complementary silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring high current capability.

MAXIMUM RATINGS (T_A=25°C)

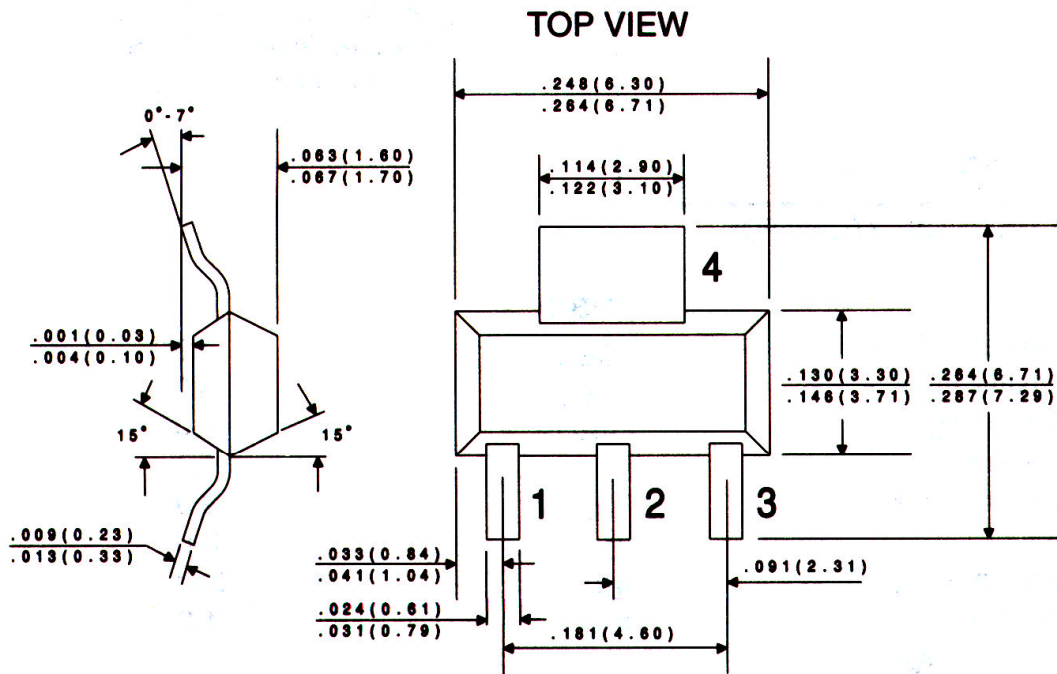
	SYMBOL		UNITS
Collector-Emitter Voltage	V _{CES}	25	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	1.0	A
Collector Current-Peak	I _{CM}	2.0	A
Base Current	I _B	100	mA
Base Current-Peak	I _{BM}	200	mA
Power Dissipation	P _D	2.0	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Q _{JA}	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =25V			10	mA
I _{CBO}	V _{CB} =25V, T _A =150°C			1.0	mA
I _{EBO}	V _{EB} =5.0V			10	mA
BV _{CBO}	I _C =10mA	25			V
BV _{CEO}	I _C =10mA	20			V
BV _{EBO}	I _E =1.0mA	5.0			V
V _{CE(SAT)}	I _C =1.0A, I _B =100mA			0.5	V
V _{BE(ON)}	V _{CE} =10V, I _C =5.0mA		0.6		V
V _{BE(ON)}	V _{CE} =1.0V, I _C =1.0A			1.0	V
h _{FE}	V _{CE} =10V, I _C =5.0mA	50			

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
h_{FE}	$V_{CE}=1.0V, I_C=500mA$	85		375	
h_{FE}	$V_{CE}=1.0V, I_C=1.0A$	60			
f_T	$V_{CE}=5.0V, I_C=10mA, f=20MHz$	65			MHz
C_{ob}	$V_{CB}=5.0V, I_E=0, F=450kHz$		25		pF

All dimensions in inches (mm).

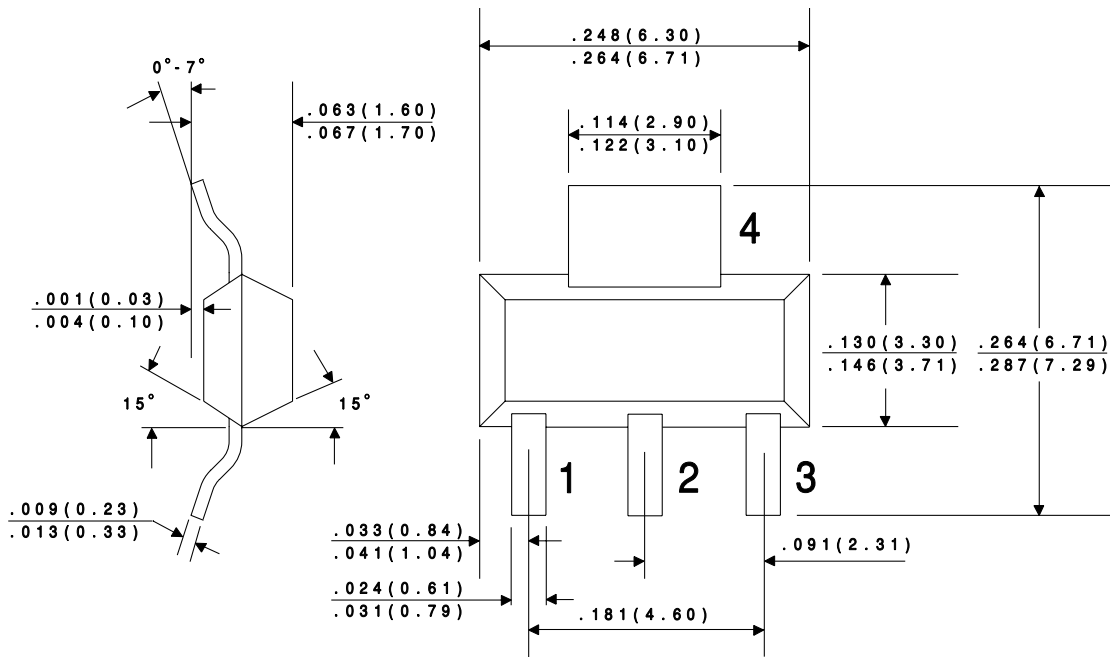


LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

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C_{ob}	$V_{CB}=5.0V, I_E=0, F=450kHz$		25		pF

All dimensions in inches (mm).



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